



1、 Electrical Parameters

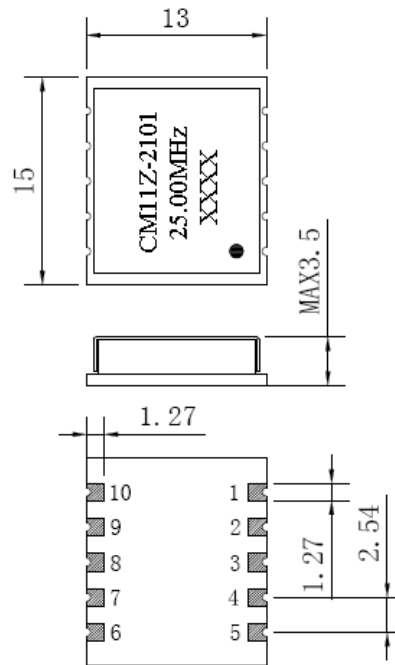
Parameters	Symbol	Electrical Spec.				Notes
		Min.	Typ.	Max.	Units	
Input						
RF Input Frequency	F_{IN}	Free Run Mode			MHz	Sel = 1
			25.00			Sel = 0
RF Input Level	V_{IN}	0.8		3.3	V	AC coupled internally
Output						
Frequency			25.00		MHz	
Output Waveform		LVCMOS				
Output High Voltage	V_{OH}	3.2		3.3	V	$V_{cc}= 3.3V, I_{OH} = 8\text{ mA}$
Output Low Voltage	V_{OL}	0.0		0.3	V	$V_{cc}= 3.3V, I_{OL} = 8\text{ mA}$
Rise / Fall Time	T_r / T_f			0.6	ns	20%-80%
Duty cycle		45	50	55	%	@50%
Start-up Time	T_S		2	10	ms	
Jitter			200	300	fs	RMS(12KHz to 20MHz)
Frequency Stabilities						
Free run Accuracy		-60		60	ppm	-40°C to +85°C
Supply Voltage						
Supply Voltage	V_{CC}	3.15	3.3	3.45	V	
Input Current	I_{CC}		30	40	mA	
Control Characteristics						
Absolute Pull Rang	APR	± 100			ppm	
Modulation BW	BW	30			Hz	
Phase Noise						
Phase Noise	Φ_n		-102	-92	dBc/Hz	100Hz
			-131	-126		1kHz
			-149	-144		10kHz
			-153	-148		100KHz
			-160	-155		1MHz



Environmental Conditions						
Operating Temperature	T _{OP}	-40	~	+85	°C	
Storage Temperature	T _{ST}	-55	~	+105	°C	
Mechanical Shock	Per MIL-STD-202,Method 213,Condition E					
Thermal Shock	Per MIL-STD-883,Method 1011,Condition A					
Soldering Conditions	Per MIL-STD-883,Method 2007,Condition A					
Shock	Leak rate less than 5 × 10 ⁻⁸ atm.cc/s of helium (crystal only)					

2、 Mechanical Structure(mm)

Pin #	Description
1	Fin
2	N/C
3	Sel
4	V _{CC}
5	Gnd
6	F _{OUT 2}
7	F _{OUT 1}
8	N/C
9	V _{CC}
10	Gnd



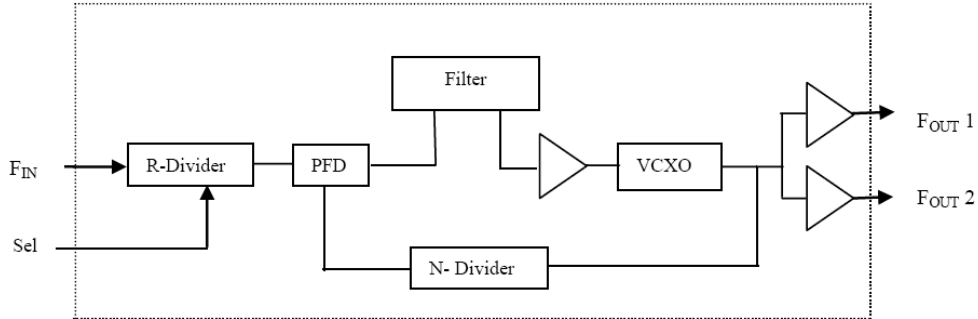
Note1: Tolerance ±0.2mm without mark

Note2: N/C is not connect

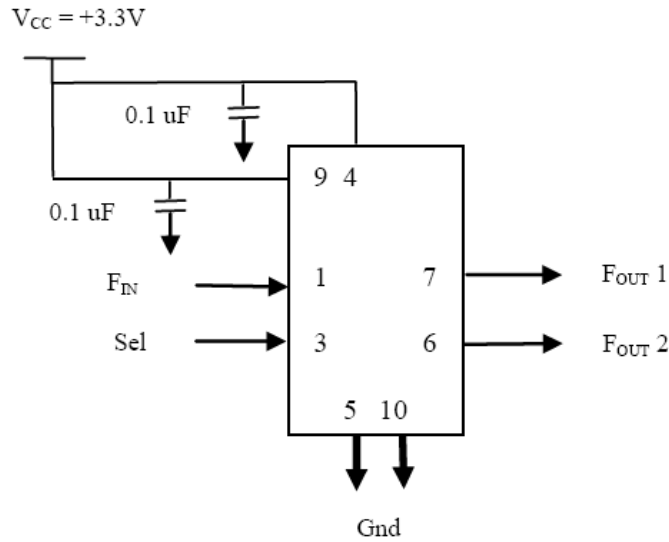
Note3: The first two xx representative: week
After two xx representative: year



3、 Block Diagram



4、 Test circuit



5、 Reflow Soldering Curve (RoHS)

